

## Chip Specification

### General Description:

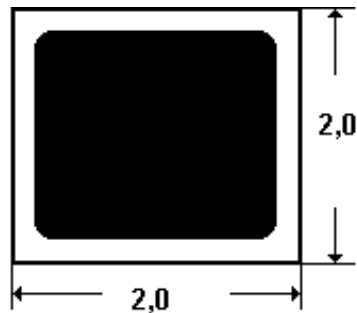
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- \* **Guard-ring for stress protection**
- \* **Extremely low forward voltage**
- \* **125 °C operation junction temperature**
- \* **reverse avalanche behavior**

### Mechanical Data:

**SB 5XX** passivated Silicon Chip

Dimension(mm)	2,0x2,0
Thickness:	350 +- 20 µm
Metallization:	
Top ( Anode ) :	Al Ag
Bottom ( Cathode ) :	TiNiAg



Forward Current(A)	5 A
Reverse Voltage (V):	23, 43, 100 V

Type	Chip	VR(V)	VF(V)@25 C at If=1A	IRM@VRMM at 25 C
	size(mm)			
SB520	2,0x2,0	23 V	450mV	0,5mA
SB540	2,0x2,0	43 V	600mV	0,5mA
SB5100	2,0x2,0	100 V	730mV	0,5mA

Note: Other voltages, Vf & Top Metal AL are available

